ABSTRACT OF THE DISCLOSURE

A solid-state imaging device is provided, which comprising at least one unit pixel portion. Each of the at least one unit pixel portion comprises a light receiving portion for subjecting incident light to photoelectric conversion to output electric charges, and an optical signal detecting portion comprising a first conductivity type buried region for accumulating the output electric charges. The light receiving portion comprises at least a portion of a second conductivity type impurity diffusion region, and at least a portion of a first conductivity type well region provided between a second conductivity type well region and the second conductivity type impurity diffusion region. The second conductivity type well region and the second conductivity type impurity diffusion region are separated from each other.